

## 2SK3211(L), 2SK3211(S)

Silicon N Channel MOS FET  
High Speed Power Switching

REJ03G1091-0400

Rev.4.00

May 15, 2006

### Features

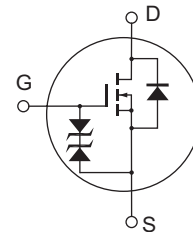
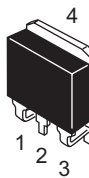
- Low on-resistance  
 $R_{DS} = 60 \text{ m}\Omega$  typ.
- High speed switching
- 4 V gate drive device can be driven from 5 V source

### Outline

RENESAS Package code: PRSS0004AE-A  
(Package name: LPAK(L))



RENESAS Package code: PRSS0004AE-B  
(Package name: LPAK(S)-(1))



1. Gate
2. Drain
3. Source
4. Drain

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DS</sub>	200	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	25	A
Drain peak current	I <sub>D(pulse)</sub> <sup>Note1</sup>	100	A
Body-drain diode reverse drain current	I <sub>DR</sub>	25	A
Avalanche current	I <sub>AP</sub> <sup>Note3</sup>	25	A
Avalanche energy	E <sub>AR</sub> <sup>Note3</sup>	41	mJ
Channel dissipation	P <sub>ch</sub> <sup>Note2</sup>	100	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%  
 2. Value at Tc = 25°C  
 3. Value at Tch = 25°C, Rg ≥ 50 Ω

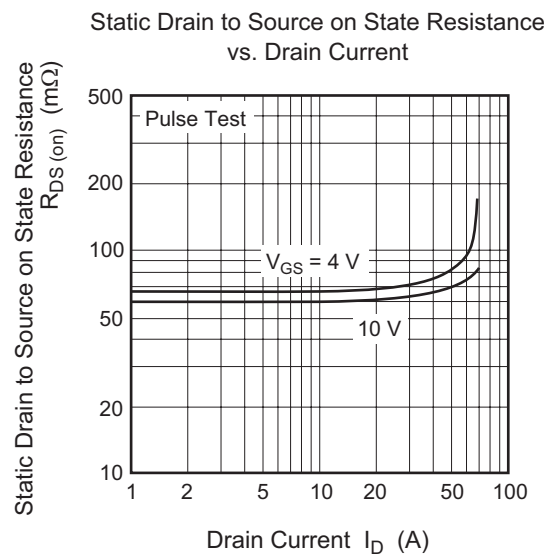
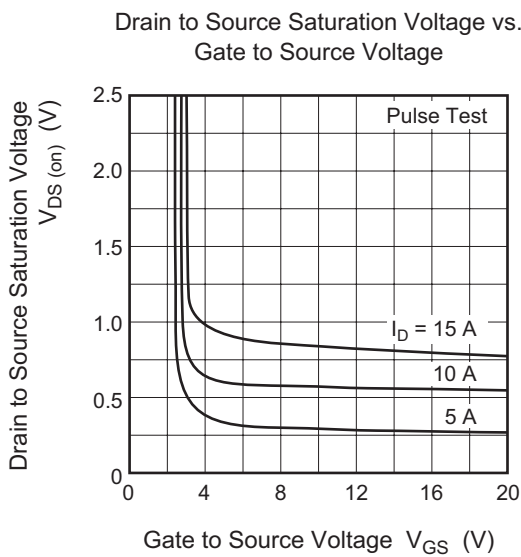
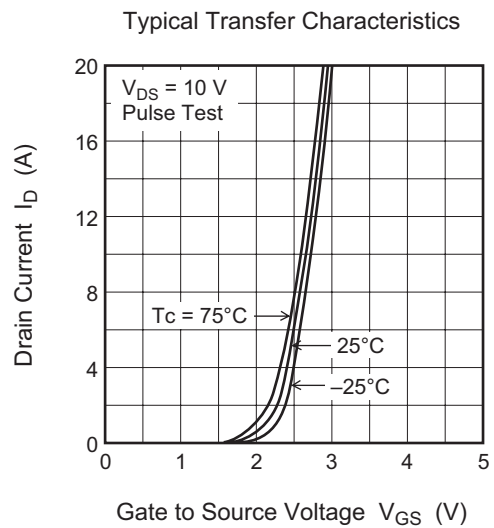
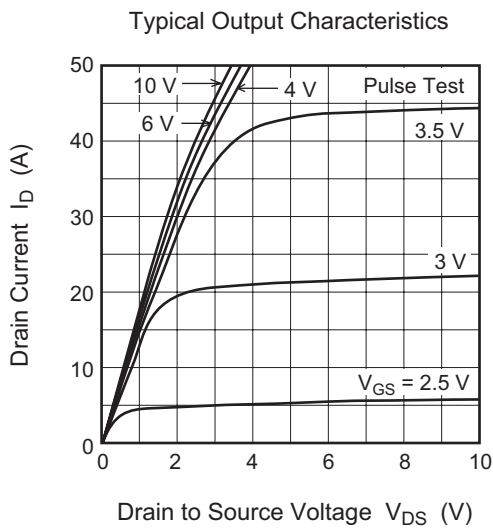
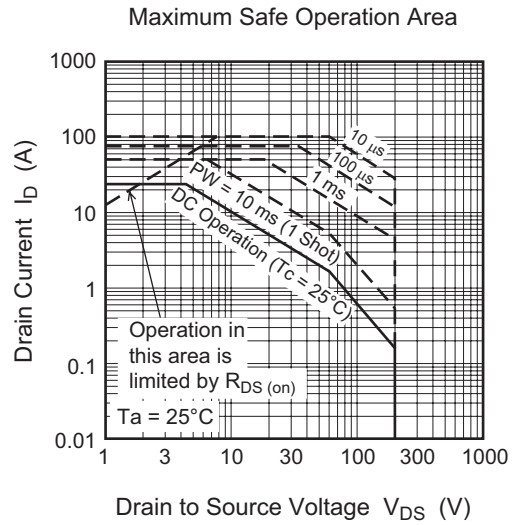
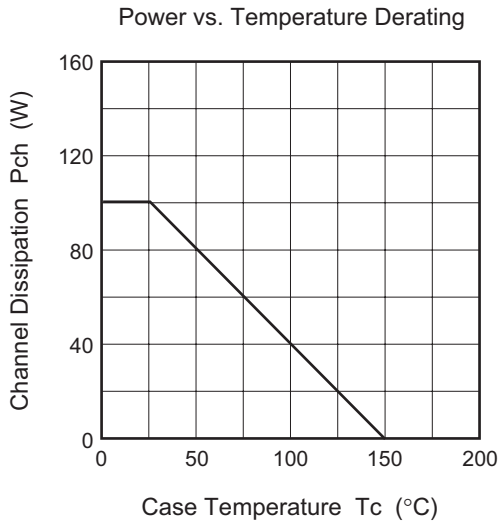
## Electrical Characteristics

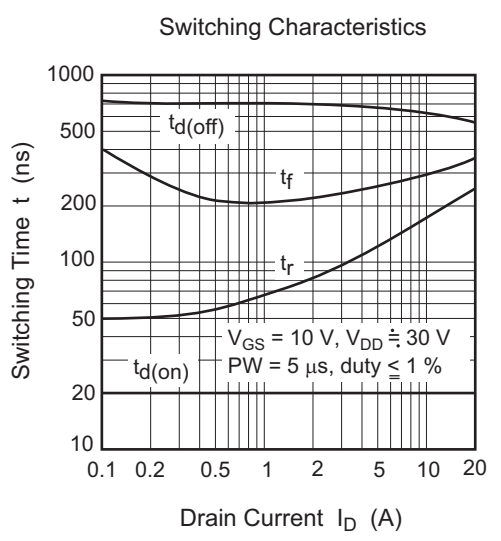
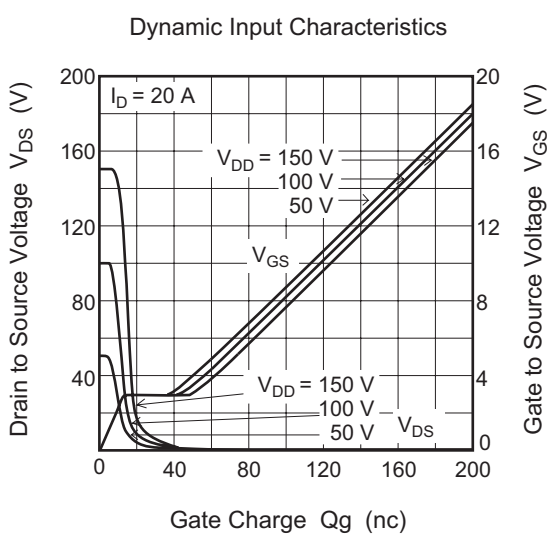
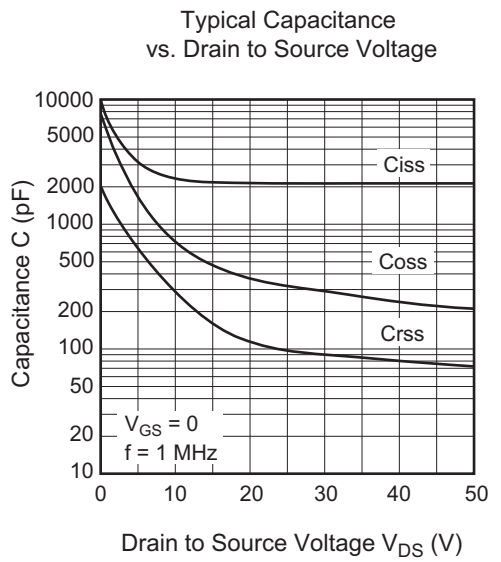
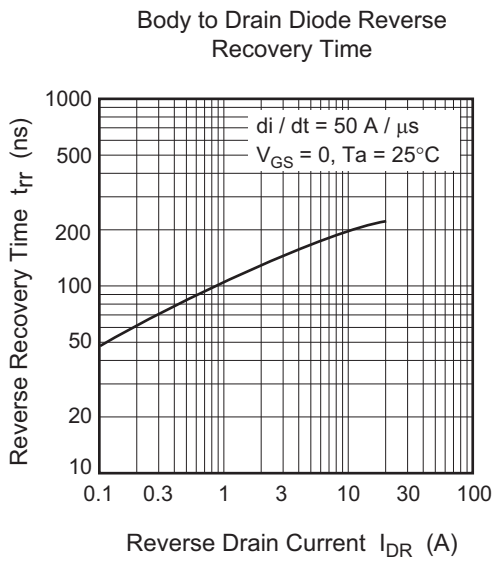
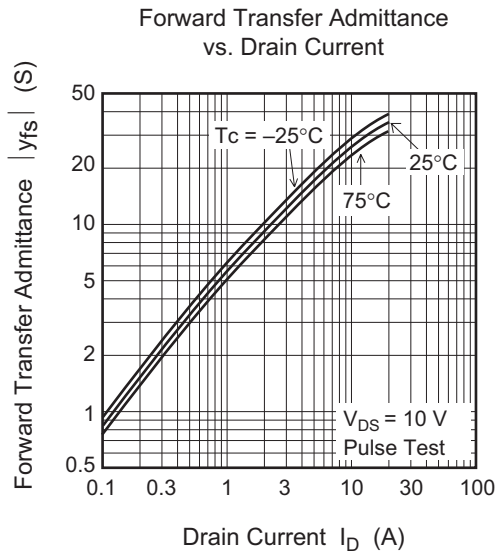
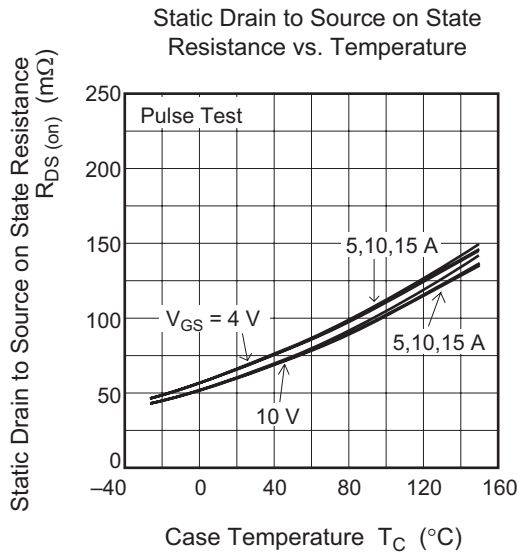
(Ta = 25°C)

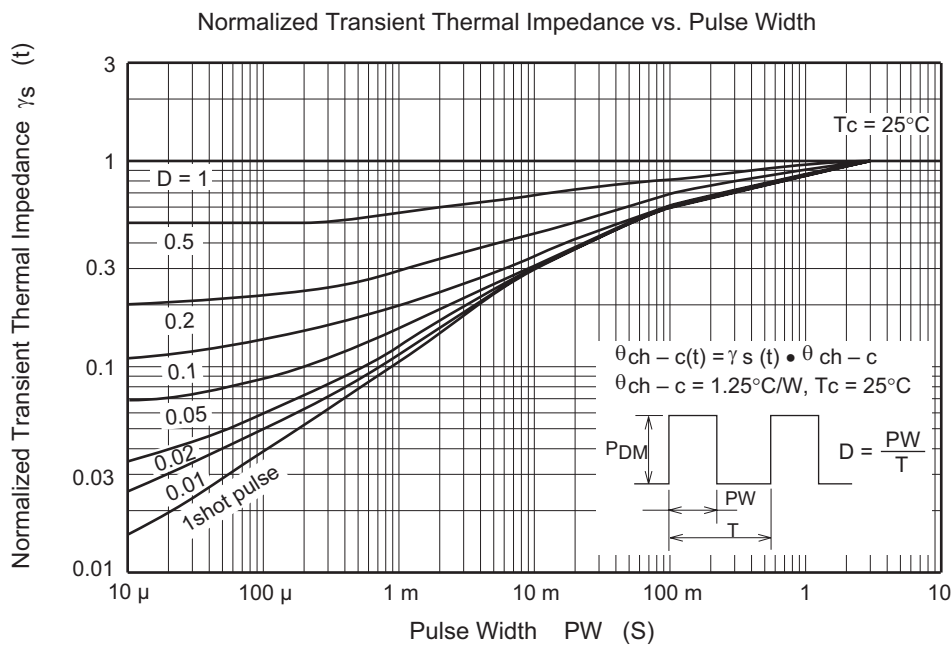
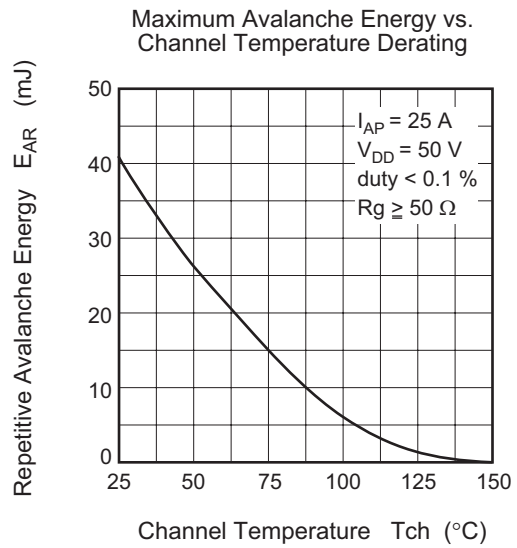
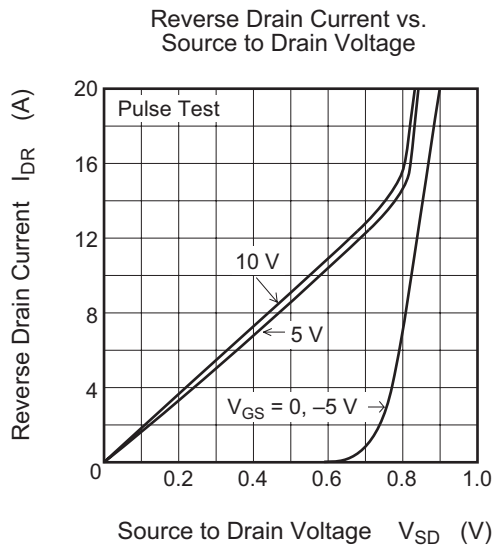
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	200	—	—	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR)GSS</sub>	±20	—	—	V	I <sub>G</sub> = ±100 μA, V <sub>DS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	10	μA	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS(off)</sub>	1.0	—	2.5	V	I <sub>D</sub> = 1 mA, V <sub>DS</sub> = 10 V
Static drain to source on state resistance	R <sub>DS(on)</sub>	—	60	75	mΩ	I <sub>D</sub> = 15 A, V <sub>GS</sub> = 10 V <sup>Note4</sup>
	R <sub>DS(on)</sub>	—	65	85	mΩ	I <sub>D</sub> = 15 A, V <sub>GS</sub> = 4 V <sup>Note4</sup>
Forward transfer admittance	y <sub>fs</sub>	18	30	—	S	I <sub>D</sub> = 15 A, V <sub>DS</sub> = 10 V <sup>Note4</sup>
Input capacitance	C <sub>iss</sub>	—	2420	—	pF	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0, f = 1 MHz
Output capacitance	C <sub>oss</sub>	—	790	—	pF	
Reverse transfer capacitance	C <sub>rss</sub>	—	340	—	pF	
Turn-on delay time	t <sub>d(on)</sub>	—	20	—	ns	I <sub>D</sub> = 15 A, V <sub>GS</sub> = 10 V, R <sub>L</sub> = 2 Ω
Rise time	t <sub>r</sub>	—	230	—	ns	
Turn-off delay time	t <sub>d(off)</sub>	—	590	—	ns	
Fall time	t <sub>f</sub>	—	330	—	ns	
Body-drain diode forward voltage	V <sub>DF</sub>	—	0.95	—	V	I <sub>F</sub> = 25 A, V <sub>GS</sub> = 0
Body-drain diode reverse recovery time	t <sub>rr</sub>	—	230	—	ns	I <sub>F</sub> = 25 A, V <sub>GS</sub> = 0 di <sub>F</sub> / dt = 50 A/ μs

Note: 4. Pulse test

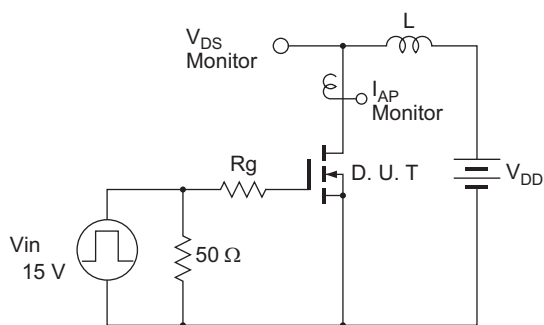
### Main Characteristics



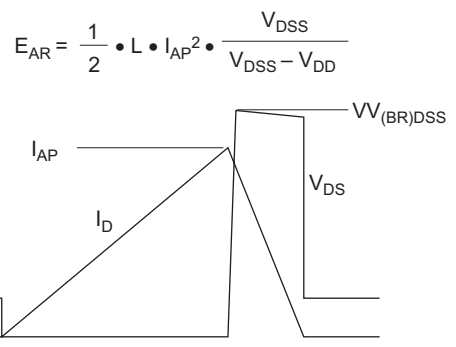


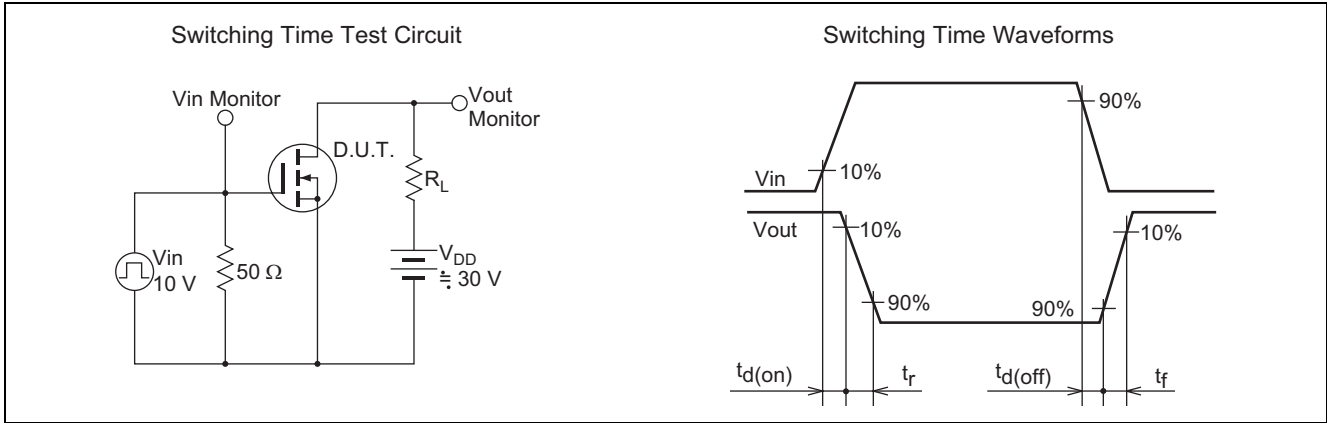


Avalanche Test Circuit

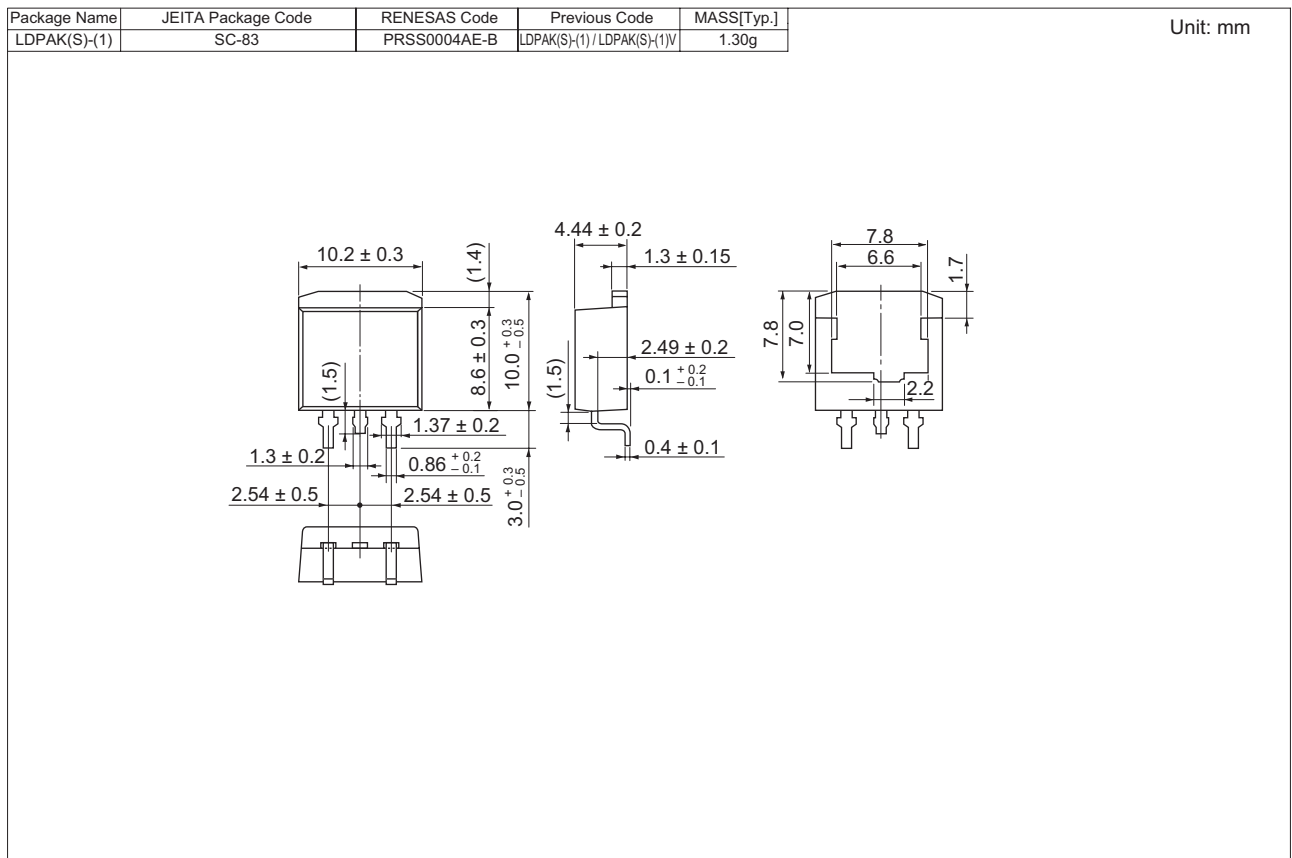
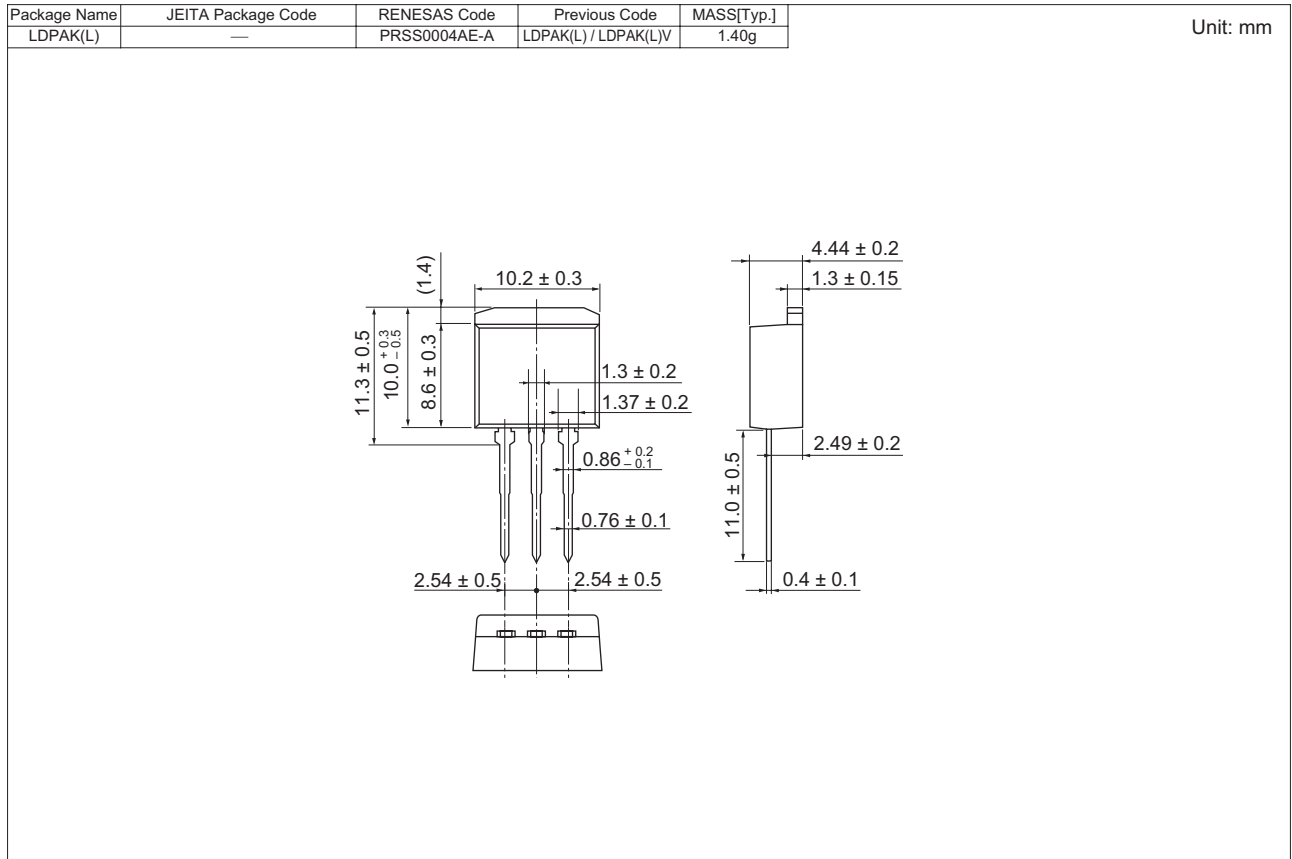


Avalanche Waveform





Package Dimensions



### Ordering Information

Part Name	Quantity	Shipping Container
2SK3211L-E	500 pcs	Box (Sack)
2SK3211STL-E	1000pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

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Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.  
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**Renesas Technology (Shanghai) Co., Ltd.**

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**Renesas Technology Hong Kong Ltd.**

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Tel: <852> 2265-6688, Fax: <852> 2730-6071

**Renesas Technology Taiwan Co., Ltd.**

10th Floor, No.99, Fushing North Road, Taipei, Taiwan  
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

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**Renesas Technology Korea Co., Ltd.**

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Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

**Renesas Technology Malaysia Sdn. Bhd**

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia  
Tel: <603> 7955-9390, Fax: <603> 7955-9510